



## MOS Controlled Diode

### PRODUCT SUMMARY

V <sub>RRM</sub>	I <sub>O</sub>	V <sub>F</sub> (MAX) @ 25°C	I <sub>R</sub> (MAX) @ 25°C
50V	10A	0.50V	0.5mA

### FEATURES

- Low Profile Design for Smart Phone Charger
- Ideal for SMT Mounting
- Low forward voltage drop
- High forward surge capability
- Excellent High Temperature Stability

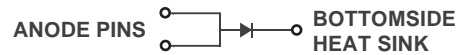
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Top View



Bottom View



### ABSOLUTE MAXIMUM RATINGS (T<sub>A</sub>=25°C unless otherwise noted)

Symbol	Parameter	Value	Unit
V <sub>RRM</sub>	Peak Repetitive Reverse Voltage	50	V
V <sub>RWM</sub>	Working Peak Reverse Voltage	50	V
V <sub>RM</sub>	DC Blocking Voltage	50	V
V <sub>R(RMS)</sub>	RMS Reverse Voltage	35	V
I <sub>O</sub>	Average Rectified Output Current	10	A
I <sub>FSM</sub>	Non-Repetitive Peak Forward Surge Current 8.3ms Single Half Sine-Wave Superimposed on Rated Load	120	A
E <sub>AS</sub>	Non-Repetitive Avalanche Energy (T <sub>J</sub> = 25°C, I <sub>AS</sub> = 10, L = 5mH)	170	mJ
P <sub>ARM</sub>	Repetitive Peak Avalanche Energy	24000	W

### THERMAL CHARACTERISTICS

Symbol	Parameter	Value	Unit
R <sub>θJA</sub>	Thermal Resistance, Junction-to-Ambient	70	°C/W
T <sub>J</sub>	Operating Temperature Range	-55 to 150	°C
T <sub>STG</sub>	Storage Temperature Range	-55 to 175	°C

### ELECTRICAL CHARACTERISTICS (T<sub>A</sub>=25°C unless otherwise specified)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V <sub>F</sub>	Forward Voltage Drop	I <sub>F</sub> = 10A, T <sub>J</sub> = 25°C		0.46	0.50	V
		I <sub>F</sub> = 10A, T <sub>J</sub> = 125°C		0.44	0.49	V
I <sub>R</sub>	Leakage Current	V <sub>R</sub> = 50V, T <sub>J</sub> = 25°C		150	500	uA
		V <sub>R</sub> = 50V, T <sub>J</sub> = 125°C			100	mA
C <sub>T</sub>	Total Capacitance	V <sub>R</sub> = 50V, f = 1MHz		155		pF

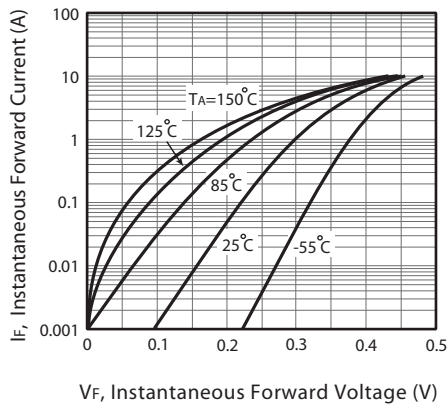


Figure 1. Typical Forward Characteristics

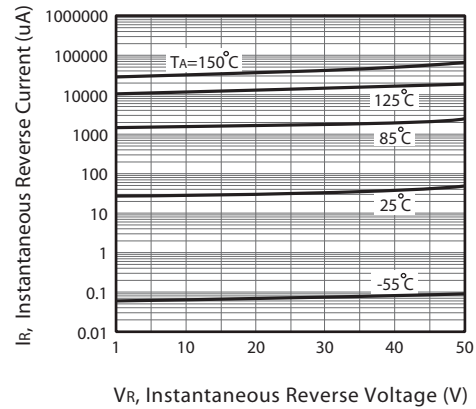


Figure 2. Typical Reverse Characteristics

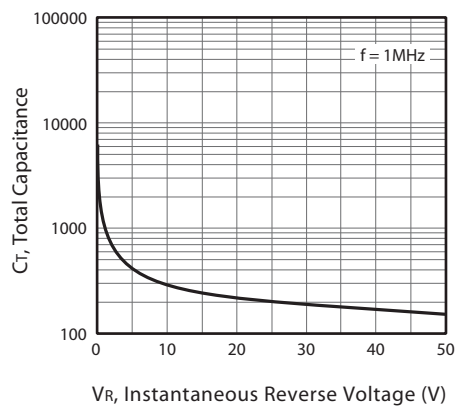


Figure 3. Total Capacitance vs. Reverse Voltage

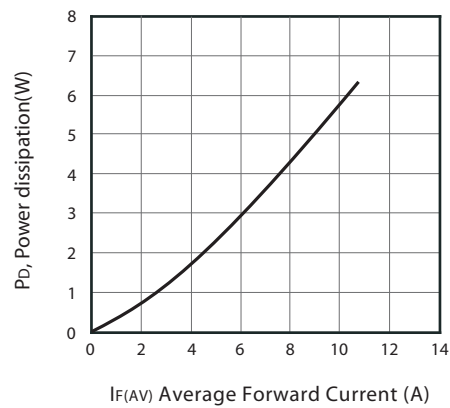


Figure 4. Forward Power Dissipation

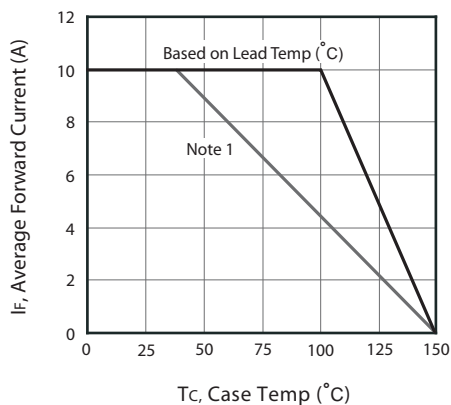


Figure 4. Forward Power Dissipation

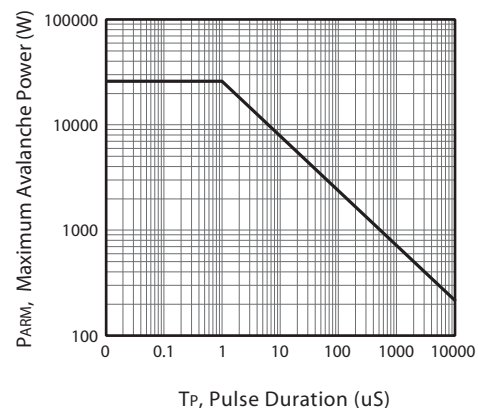


Figure 6. Maximum Avalanche Power Curve

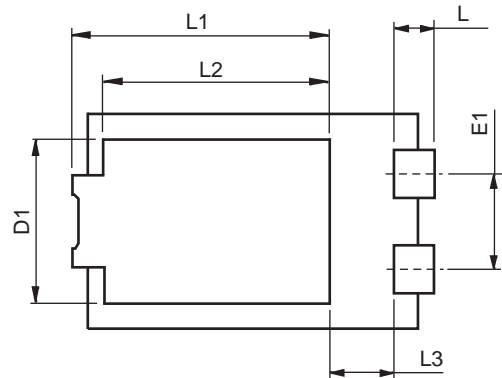
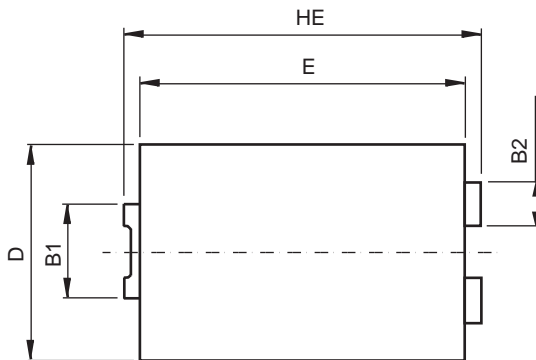
**Note :** 1.Device mounted on FR-4 substrate, 2oz copper.

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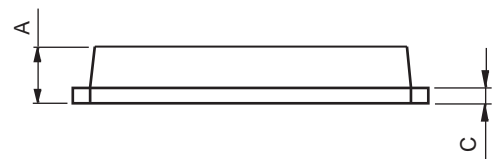
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## PACKAGE OUTLINE DIMENSIONS

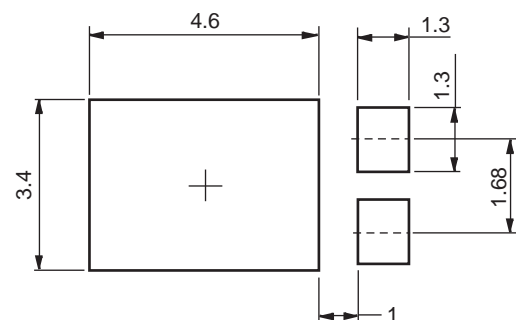
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SYMBOLS	MILLIMETERS	
	MIN.	MAX.
HE	6.40	6.60
E	5.60	5.80
D	4.10	4.30
B1	1.70	1.90
B2	0.80	1.00
A	1.05	1.20
C	0.30	0.40
L	0.85	1.10
L1	4.20	4.40
L2	3.52 Typ.	
L3	1.10	1.40
D1	3.00	3.30
E1	1.86 Typ.	



### Mounting Pad Layout (unit:mm)

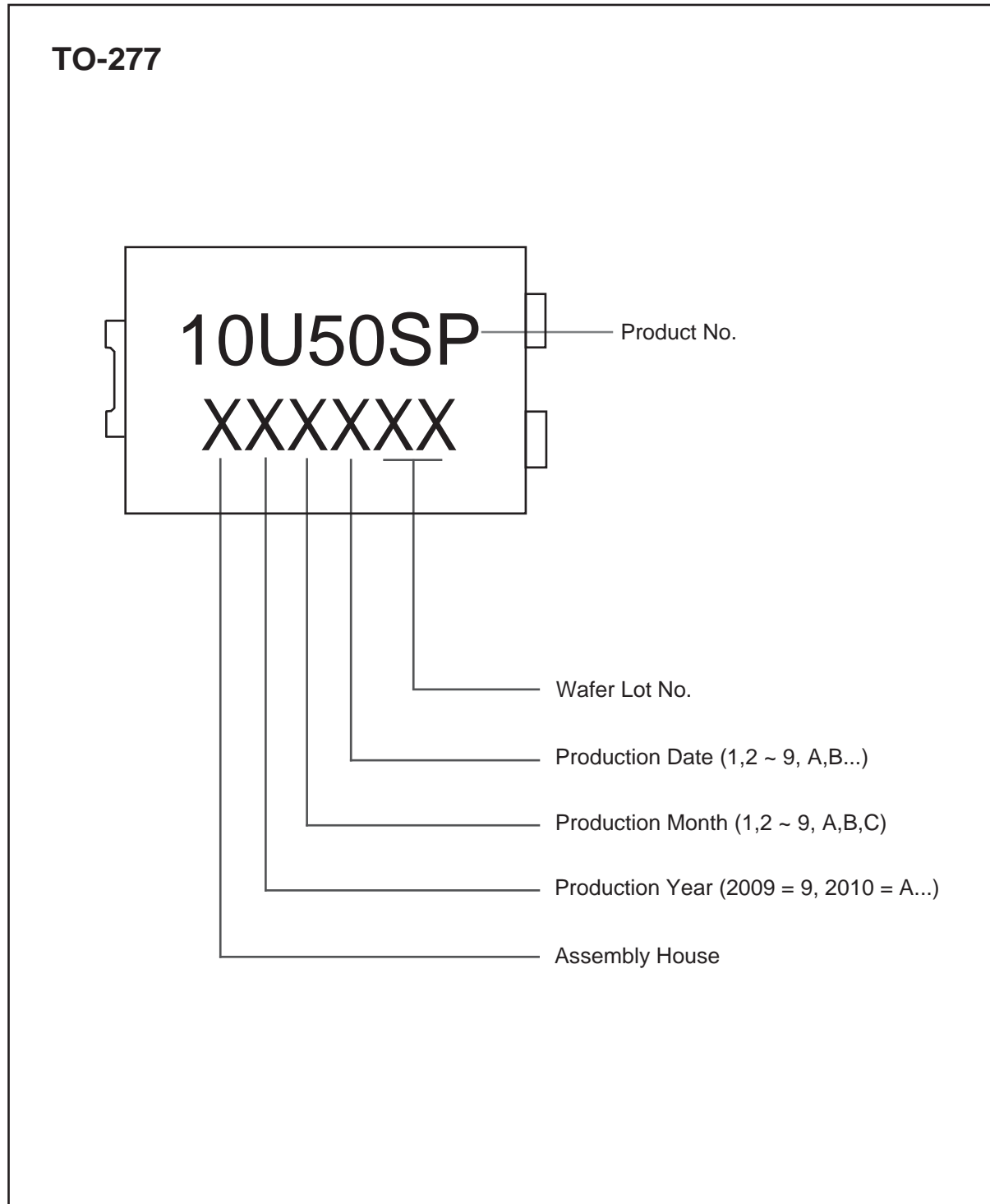


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## TOP MARKING DEFINITION



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